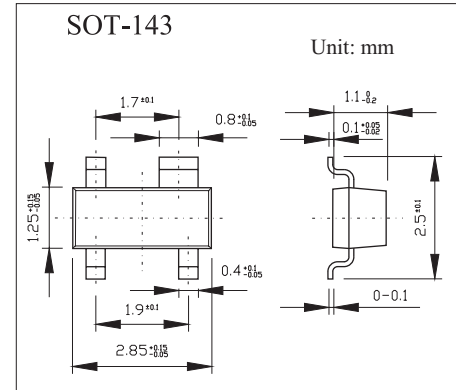


## Silicon RF Switching Diode

## BAR65-07

## ■ Features

- Low loss, low capacitance PIN-Diode
- Band switch for TV-tuners
- Series diode for mobile communications transmit-receive switch
- Unconnected pair

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	30	V
Forward current	$I_F$	100	mA
Operating temperature range	$T_{op}$	-55 to +125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note

1. Unit Rating.Total Rating = Unit Rating  $\times$  1.5

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	$I_R$	$V_R = 20\text{ V}; T_a = 25^\circ\text{C}$			20	nA
Forward voltage	$V_F$	$I_F = 100\text{ mA}$		0.93	1	V
Diode capacitance	$C_T$	$V_R = 1\text{ V}, f = 1\text{ MHz}$		0.6	0.9	pF
		$V_R = 3\text{ V}, f = 1\text{ MHz}$		0.57	0.8	
Forward resistance	$r_f$	$I_F = 5\text{ mA}, f = 100\text{ MHz}$		0.65	0.95	$\Omega$
		$I_F = 10\text{ mA}, f = 100\text{ MHz}$		0.56	0.9	
Series inductance	$L_s$			1.4		nH

## ■ Marking

Type	BAR65-07
Marking	M